PROCESS BATCH SHEET (RCA clean) **Issue 8** **Page____of____**

ENSC Batch No.______________________Wafers Started____________Date_________________________
Material________________Orientation_______________Size_______________Thickness________________
Resistivity__________________________________Type____
Wafer Vendor______________________Vendor Batch #____________________SFU P.O.________________

Process Step #	Process Conditions	Oper & Wafer #	Comments
_____A	**RCA SC-1 Clean (Organics)** Temp = 80 +/- 5C Time = 10 minutes DI H2O 5 parts (1000 mL) NH4OH, 30% 1 part (200 mL) H2O2, 50% 1 part (200 mL)* *Volumes are sufficient to cover 8 wafers in dippers in 2000 mL glass beaker, major flats up.		Hydrate wafers in DI water before placing in SC-1. Heat water for SC-1. Add NH4OH and then H2O2. Stabilize temperature. Remove wafers from water, place in SC-1, and begin timing if temp in range.
_____B	**DI Water Rinse** > 3 minutes in running DI H2O		
_____C	**HF Dip (Native Oxide Strip)** Temp = Room temp Time = 30 seconds DI H2O 10 parts (1500 mL) HF 1 part (150 mL)* Volumes sufficient to cover 8 wafers in dippers in 2 L plastic beaker, major flats up.		
_____D	**DI Water Rinse** > 3 minutes in running DI H2O		
_____E	**RCA SC-2 Clean (Metals)** Temp = 80 +/- 5C Time = 10 minutes DI H20 6 parts (1050 mL) HCl, 38% 1 part (175 mL) H2O2, 50% 1 part (175 mL)		Heat water. Add HCl and then H2O2. Note that addition of HCl may cause solution temperature to rise significantly. Stabilize temperature. Remove wafers from rinse, place in SC-2, and begin timing if temp in range.
_____F	**DI Water Dump Rinse** > 5 minutes in beaker of running DI water. Dump beaker. Repeat two more times.		
_____G	**Spin Dry** Spin at max RPM until dry (false colours disappear). Check for water on back. Repeat spin and/or blow dry with dry N2.		